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U.S. Patent Application Serial No. 09/532,786
Attorney Docket No. 000351

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **HAYASHI, Nobuhiko**

Serial No.: **09/532,786**

Filed: **March 22, 2000**

Group Art Unit: **2828**

Examiner: **Tuan M. Nguyen**

For: **SEMICONDUCTOR LASER DEVICE AND METHOD OF FABRICATING THE SAME**

AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents
Washington, D.C. 20231

December 12, 2002

Sir:

In response to the Office Action dated **July 12, 2002**, extended to **December 12, 2002** by a 2 month Petition for Extension of Time, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1 and 11 as indicated below:

1. (Amended) A semiconductor laser device comprising:

a first nitride based semiconductor layer including a light emitting layer and containing at least one of indium, gallium, aluminum, boron and thallium;